

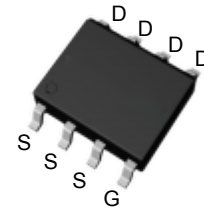
Features

- 60V/16A
 $R_{DS(ON)} = 9m\Omega (typ.) @ V_{GS} = 10V$
 $R_{DS(ON)} = 12m\Omega (typ.) @ V_{GS} = 4.5V$
- 100% UIS + R_g Tested
- Reliable and Rugged
- Lead Free and Green Devices Available
(RoHS Compliant)
- Moisture Sensitivity Level MSL1
(per JEDEC J-STD-020D)

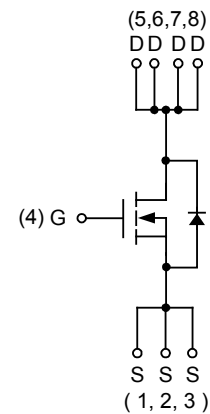
Applications

- Secondary Side Synchronous Rectification
- DC-DC Converter
- Motor Control
- Load Switching

Pin Description



Top View of SOP-8



N-Channel MOSFET

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ Unless Otherwise Noted)

Symbol	Parameter		Rating	Unit
Common Ratings				
V _{DSS}	Drain-Source Voltage		60	V
V _{GSS}	Gate-Source Voltage		±20	
T _J	Maximum Junction Temperature		150	°C
T _{STG}	Storage Temperature Range		-55 to 150	
I _S	Diode Continuous Forward Current	T _A =25°C	16	A
I _D	Continuous Drain Current	T _A =25°C	16	A
		T _A =70°C	14.4	
I _{DM} ^a	Pulsed Drain Current	T _A =25°C	48	
P _D	Maximum Power Dissipation	T _A =25°C	1.79	W
		T _A =70°C	1.14	
R _{θJA} ^c	Thermal Resistance-Junction to Ambient	Steady state	70	°C/W
I _{AS} ^b	Avalanche Current, Single pulse	L=0.5mH	36	A
E _{AS} ^b	Avalanche Energy, Single pulse	L=0.5mH	324	mJ

Note a : Pulse width limited by max. junction temperature.

Note b : UIS tested and pulse width limited by maximum junction temperature 150°C (initial temperature $T_J=25^{\circ}\text{C}$).

Note c : Surface Mounted on 1in^2 pad area.

Electrical Characteristics ($T_A = 25^\circ\text{C}$ unless otherwise noted)

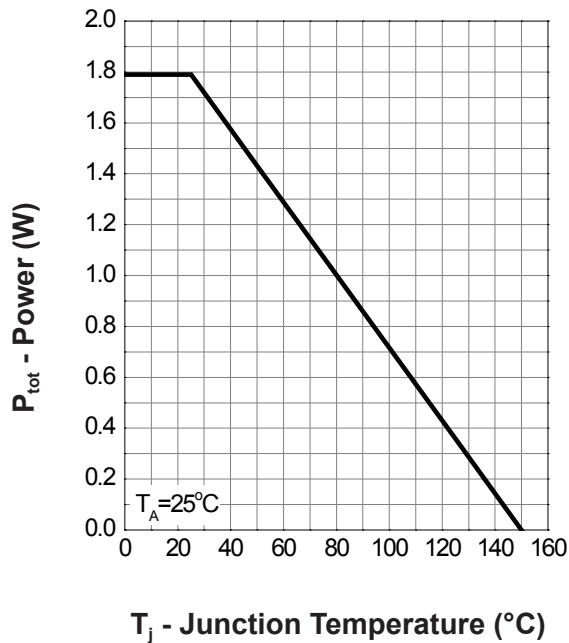
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
Static Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _{DS} =250μA	60	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} =48V, V _{GS} =0V	-	-	1	μA
		T _j =85°C	-	-	30	
V _{GS(th)}	Gate Threshold Voltage	V _{DS} =V _{GS} , I _{DS} =250μA	1	2	3	V
I _{GSS}	Gate Leakage Current	V _{GS} =±20V, V _{DS} =0V	-	-	±100	nA
R _{DS(ON)} ^d	Drain-Source On-state Resistance	V _{GS} =10V, I _{DS} =8A	-	9	12	mΩ
		V _{GS} =4.5V, I _{DS} =7A	-	12	15	
Diode Characteristics						
V _{SD} ^d	Diode Forward Voltage	I _{SD} =2A, V _{GS} =0V	-	0.8	1.3	V
t _{rr}	Reverse Recovery Time	I _{SD} =8A, dI _{SD} /dt=100A/μs	-	24	-	ns
Q _{rr}	Reverse Recovery Charge		-	25	-	nC
Dynamic Characteristics ^e						
R _G	Gate Resistance	V _{GS} =0V,V _{DS} =0V,F=1MHz	-	1.5	-	Ω
C _{iss}	Input Capacitance	V _{GS} =0V, V _{DS} =30V, Frequency=1.0MHz	-	2400	-	pF
C _{oss}	Output Capacitance		-	198	-	
C _{rss}	Reverse Transfer Capacitance		-	149	-	
t _{d(ON)}	Turn-on Delay Time	V _{DD} =30V, R _L =30Ω, I _{DS} =1A, V _{GEN} =10V, R _G =6Ω	-	16	29	ns
t _r	Turn-on Rise Time		-	9	17	
t _{d(OFF)}	Turn-off Delay Time		-	59	107	
t _f	Turn-off Fall Time		-	16	29	
Gate Charge Characteristics ^e						
Q _g	Total Gate Charge	V _{DS} =30V, V _{GS} =10V, I _{DS} =8A	-	47.5	-	nC
Q _{gs}	Gate-Source Charge		-	5.7	-	
Q _{gd}	Gate-Drain Charge		-	13.7	-	

Note d : Pulse test ; pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$.

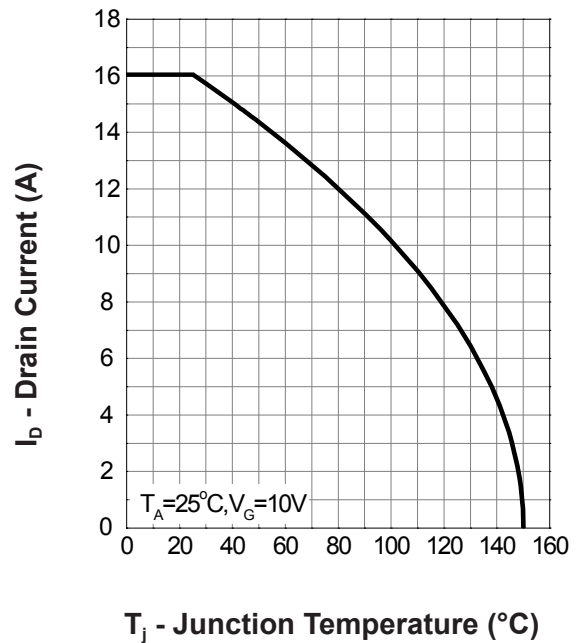
Note e : Guaranteed by design, not subject to production testing.

Typical Operating Characteristics

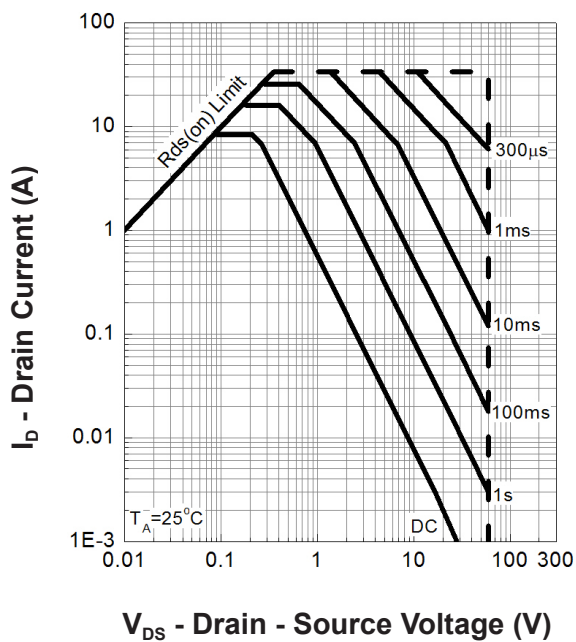
Power Dissipation



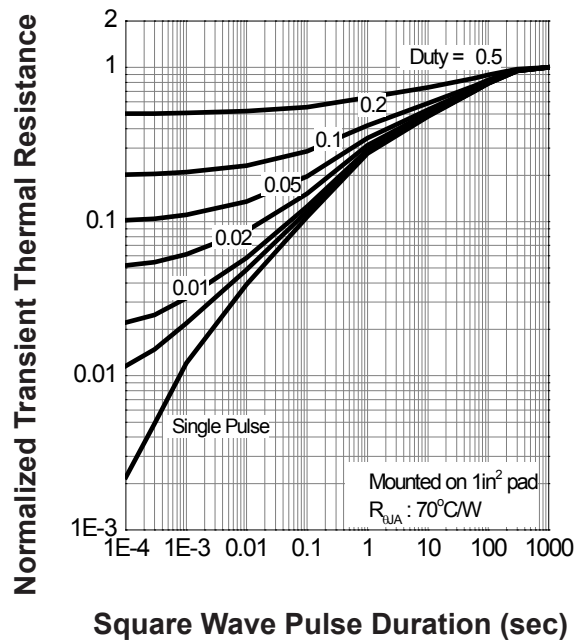
Drain Current



Safe Operation Area

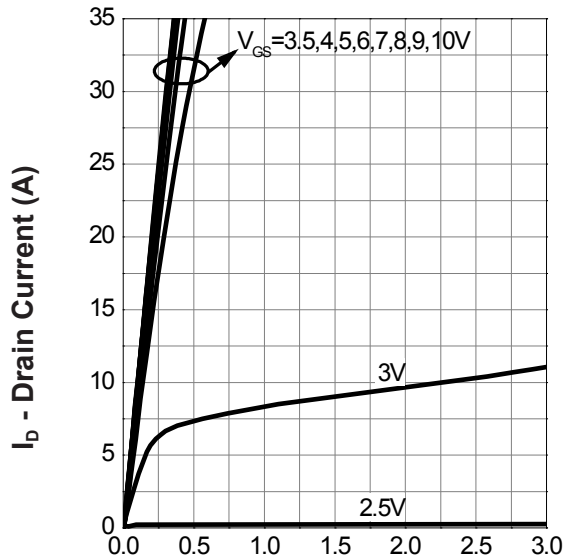


Thermal Transient Impedance



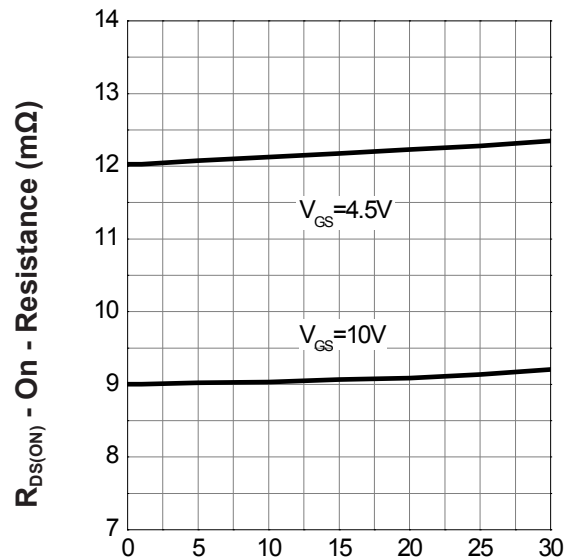
Typical Operating Characteristics(Cont.)

Output Characteristics



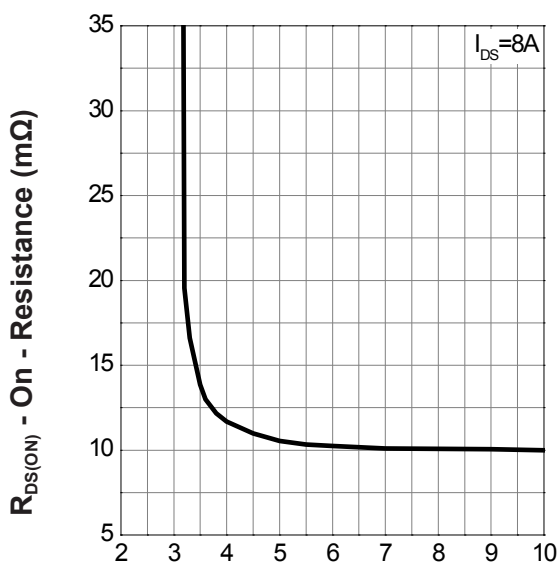
V_{DS} - Drain - Source Voltage (V)

Drain-Source On Resistance



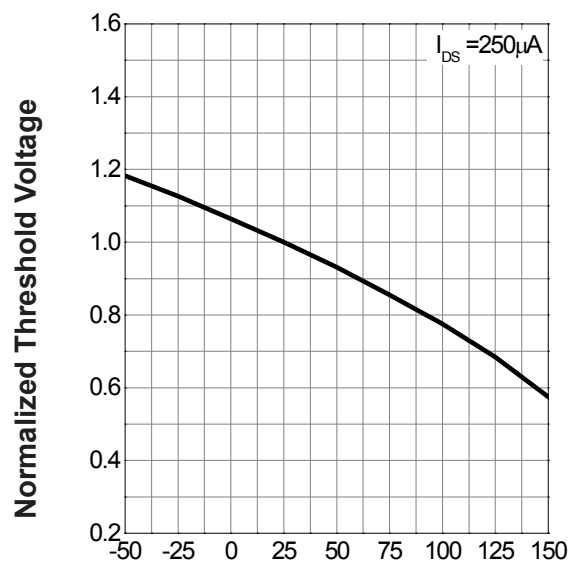
I_D - Drain Current (A)

Gate-Source On Resistance



V_{GS} - Gate - Source Voltage (V)

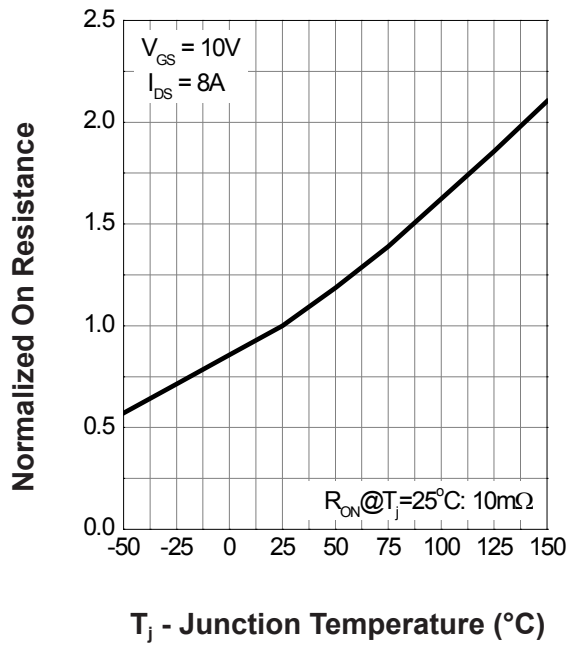
Gate Threshold Voltage



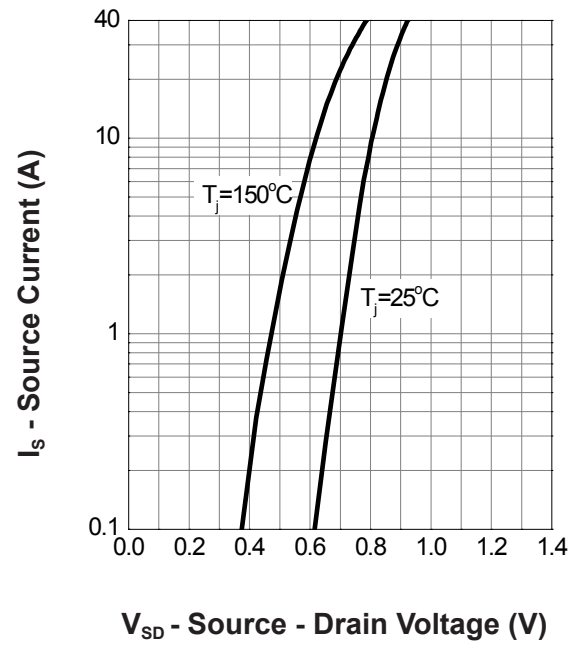
T_J - Junction Temperature ($^{\circ}C$)

Typical Operating Characteristics(Cont.)

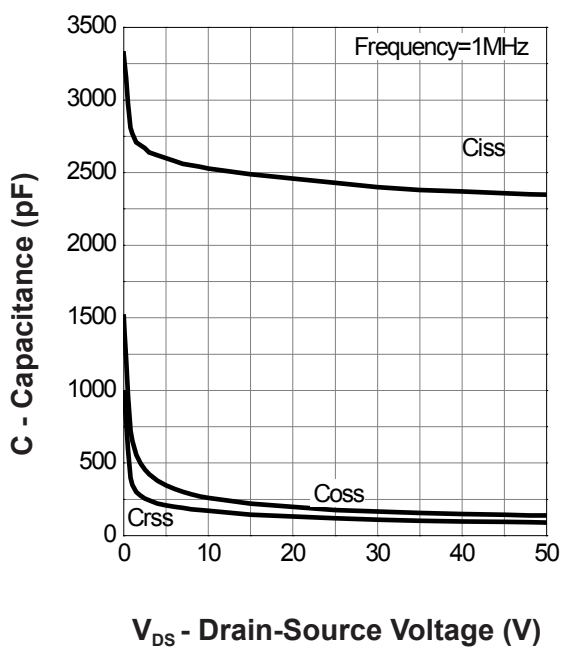
Drain-Source On Resistance



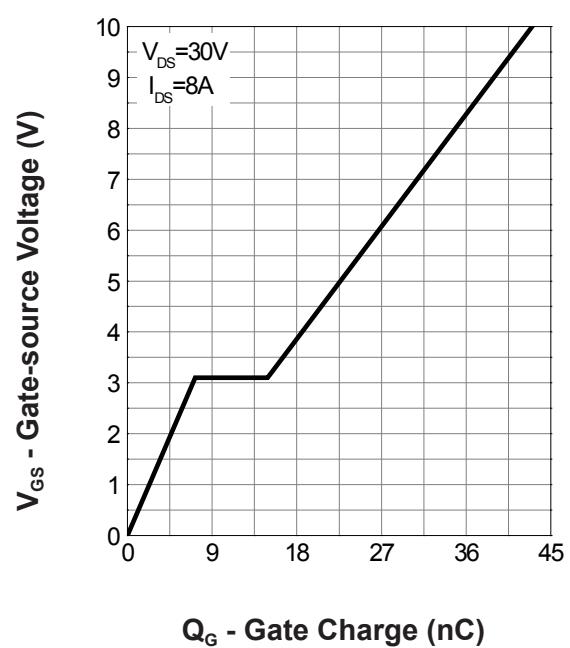
Source-Drain Diode Forward



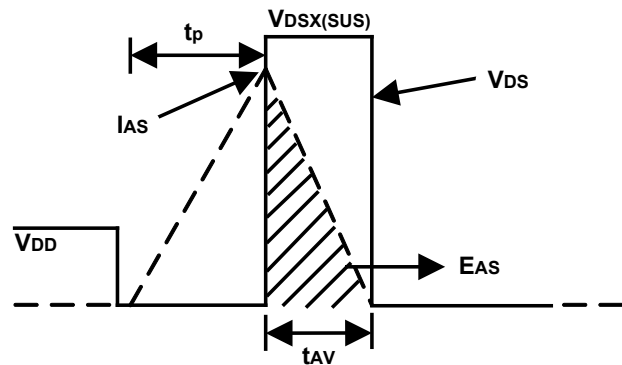
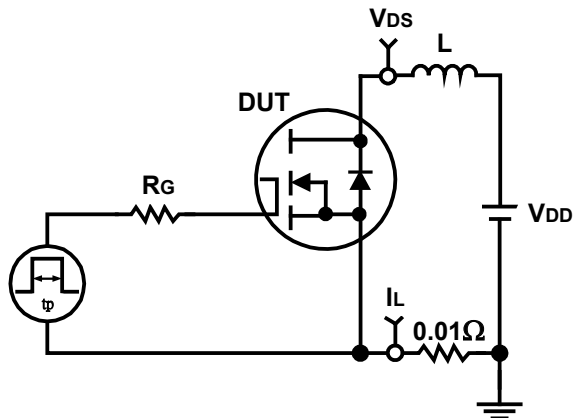
Capacitance



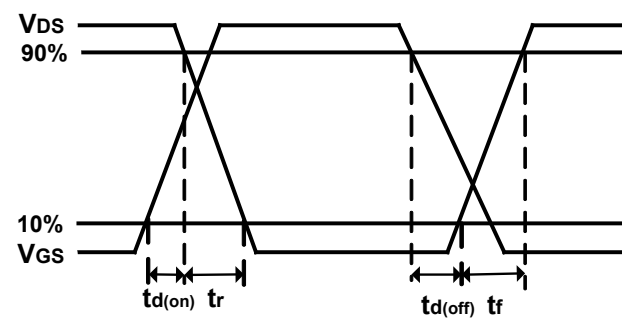
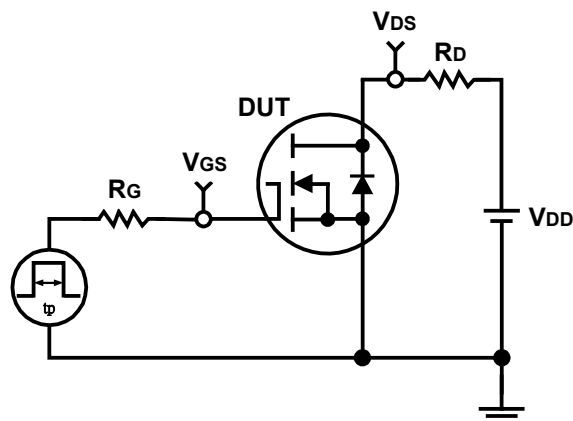
Gate Charge



Avalanche Test Circuit and Waveforms

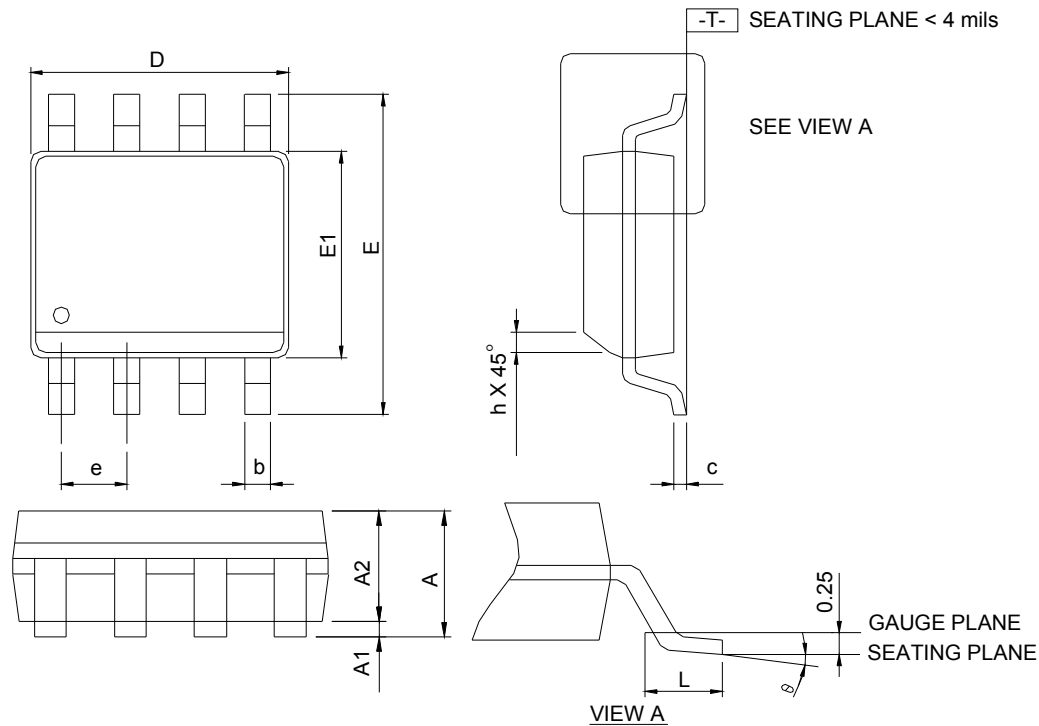


Switching Time Test Circuit and Waveforms



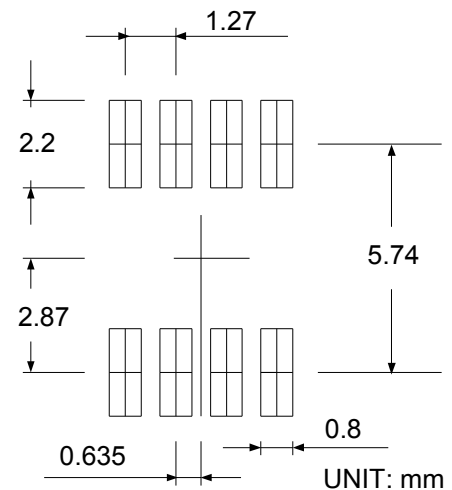
Package Information

SOP-8



SYMBOL	SOP-8			
	MILLIMETERS		INCHES	
	MIN.	MAX.	MIN.	MAX.
A	-	1.75	-	0.069
A1	0.10	0.25	0.004	0.010
A2	1.25	-	0.049	-
b	0.31	0.51	0.012	0.020
c	0.17	0.25	0.007	0.010
D	4.80	5.00	0.189	0.197
E	5.80	6.20	0.228	0.244
E1	3.80	4.00	0.150	0.157
e	1.27 BSC		0.050 BSC	
h	0.25	0.50	0.010	0.020
L	0.40	1.27	0.016	0.050
θ	0°	8°	0°	8°

RECOMMENDED LAND PATTERN



Note: 1. Follow JEDEC MS-012 AA.

2. Dimension D" does not include mold flash, protrusions or gate burrs. Mold flash, protrusion or gate burrs shall not exceed 6 mil per side.
3. Dimension E" does not include inter-lead flash or protrusions. Inter-lead flash and protrusions shall not exceed 10 mil per side.